

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	20	V		
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 6) V 45V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	9.0 7.2	А
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	$T_C = +25$ °C $T_C = +70$ °C	I_D	21 17	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	70	Α		
Continuous Source-Drain Diode Current (Note 6)	I _S	3	Α		
Pulsed Source-Drain Diode Current (10µs Pulse, Du	sed Source-Drain Diode Current (10µs Pulse, Duty Cycle = 1%)		I _{SM}	25	Α
Avalanche Current (Note 7) L = 0.1mH	I _{AS}	18	Α		
Avalanche Energy (Note 7) L = 0.1mH			E _{AS}	17	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$T_A = +25$ °C	P_{D}	0.9	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	144	°C/W	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	P _D	1.3	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	93	°C/W	
Thermal Resistance, Junction to Case (Note 6)	Steady State	R ₀ JC	16		
Operating and Storage Temperature Range		$T_{J_i} T_{STG}$	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	_	_	1	μA	V _{DS} = 16V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±10	μA	$V_{GS} = \pm 10V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	0.4	_	1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			7.2	11	mΩ	$V_{GS} = 4.5V, I_D = 7A$	
Static Drain-Source On-Resistance	D		9.0	13		$V_{GS} = 2.5V, I_D = 7A$	
Static Dialit-Source Off-Resistance	R _{DS(ON)}		11.5	25		$V_{GS} = 1.8V, I_D = 5A$	
			19.1	50		$V_{GS} = 1.5V, I_D = 3A$	
Diode Forward Voltage	V_{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_S = 8.5A$	
DYNAMIC CHARACTERISTICS (Note 9)			•	•		•	
Input Capacitance	C _{ISS}	_	2,248	_	pF		
Output Capacitance	Coss	-	295	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	C _{RSS}	_	265	_	pF	T = 1.0MH2	
Gate Resistance	R _G	_	1.5	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_{G}	_	24	_	nC		
Total Gate Charge (V _{GS} = 10V)	Q_{G}	_	56	_	nC	7, 40,4 0.54	
Gate-Source Charge	Q _{GS}	_	3.5	_	nC	$V_{DS} = 10V, I_D = 8.5A$	
Gate-Drain Charge	Q_{GD}	_	5.1	_	nC	7	
Turn-On Delay Time	t _{D(ON)}	_	3.6	_	ns		
Turn-On Rise Time	t _R	_	2.6	_	ns	$V_{DS} = 10V, I_{D} = 8.5A$	
Turn-Off Delay Time	t _{D(OFF)}	_	21.6	_	ns	$V_{GS} = 4.5V, R_{G} = 1.8\Omega$	
Turn-Off Fall Time	t _F	_	13.5	_	ns	1	
Reverse Recovery Time	t _{RR}	_	12.8	_	ns	I _F = 8.5A, di/dt = 210A/μs	
Reverse Recovery Charge	Q _{RR}	_	6.9	_	nC		

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

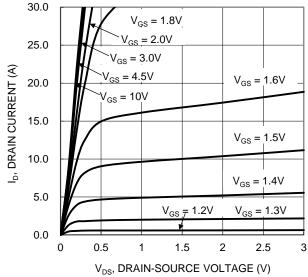
^{6.} Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

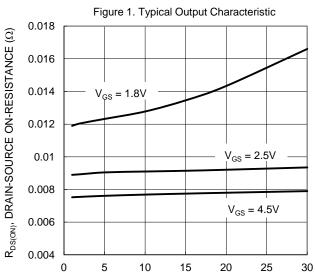
^{7.} IAS and EAS ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

^{8.} Short duration pulse test used to minimize self-heating effect.

^{9.} Guaranteed by design. Not subject to product testing.







I_D, DRAIN-SOURCE CURRENT (A) Figure 3. Typical On-Resistance vs. Drain Current

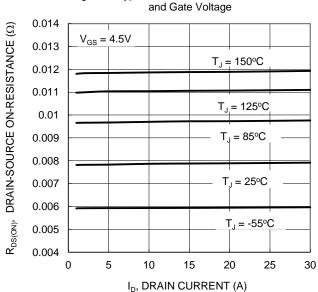


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

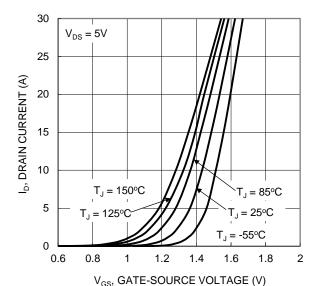


Figure 2. Typical Transfer Characteristic

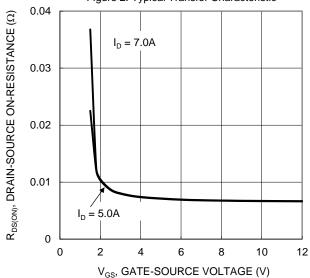


Figure 4. Typical Transfer Characteristic

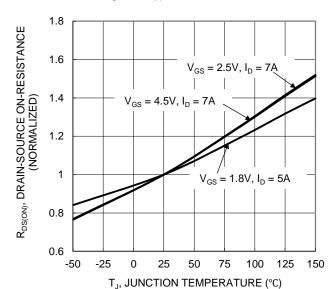


Figure 6. On-Resistance Variation with Junction Temperature





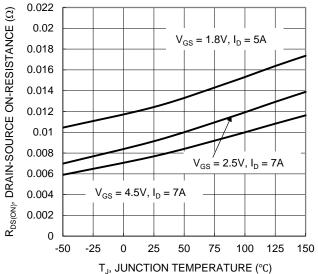
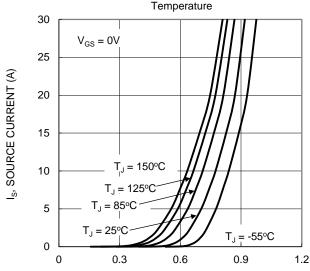


Figure 7. On-Resistance Variation with Junction Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

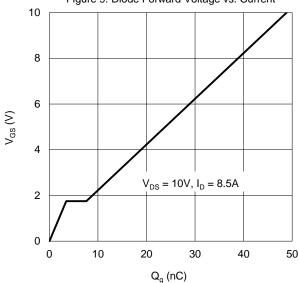


Figure 11. Gate Charge

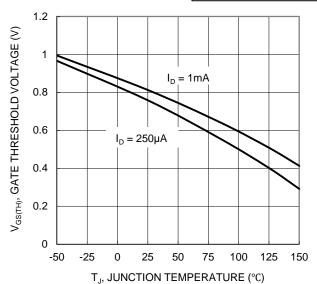


Figure 8. Gate Threshold Variation vs. Junction Temperature

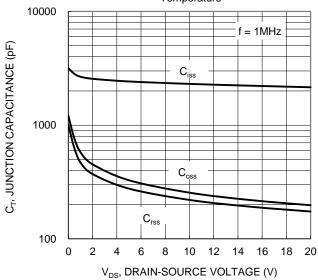
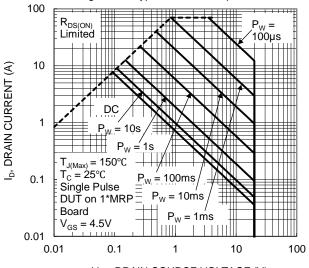


Figure 10. Typical Junction Capacitance



V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



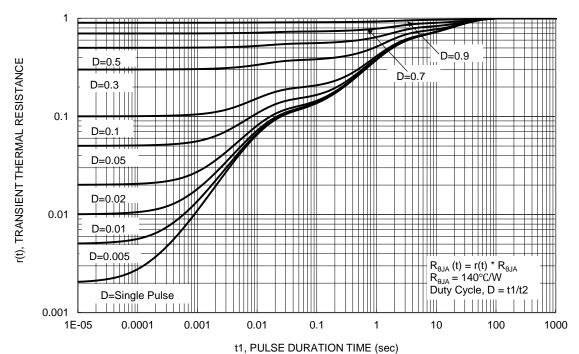


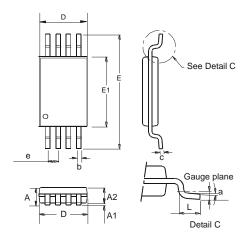
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSSOP-8

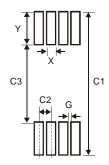


TSSOP-8					
Dim	Min	Max	Тур		
а	0.09	-	-		
Α	-	1.20	-		
A1	0.05	0.15	_		
A2	0.825	1.025	0.925		
b	0.19	0.30	-		
С	0.09	0.20	-		
D	2.90	3.10	3.025		
е	_	_	0.65		
E	_	_	6.40		
E1	4.30	4.50	4.425		
L	0.45	0.75	0.60		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TSSOP-8



Dimensions	Value (in mm)		
X	0.45		
Υ	1.78		
C1	7.72		
C2	0.65		
C3	4.16		
G	0.20		



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